

PLASMA-ENHANCED CHEMICAL VAPOR DEPOSITION

What We Offer

Design &
Simulation



Prototyping &
Fabrication



Testing &
Characterization



Plasma-Enhanced Chemical Vapor Deposition (PECVD) is a versatile thin-film deposition technique that uses plasma to enable low-temperature growth of high-quality dielectric and semiconductor films.

Key applications

**Dielectric and
insulating layers**

**Surface passivation
and protection**

**Thin-film
coatings**

PlasmaPro 80 Oxford Instruments Plasma Technology

- Growth temperature between: 225 – 300 °C
- Working pressure: 500 – 1500 mTorr
- Process gases: SiH_4 , N_2 , Ar, NH_3 , N_2O , CF_4
- Wafer size up to 4"

Materials for deposition:

- SiN_x
- SiO_2

Cleanroom class: ISO7

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Features

- Dual plasma source: high and low frequencies for film stress control
- Gas injection through a "showerhead" inlet to ensure uniform growth

